





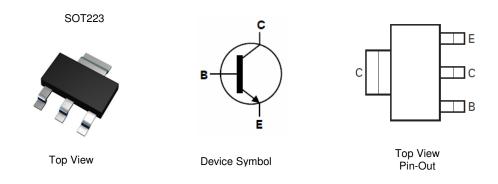
150V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 150V
- I_C = 1A High Continuous Current
- Low Saturation Voltage
- Complementary PNP Type FZT755
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 <a>®
- Weight: 0.112 grams (Approximate)



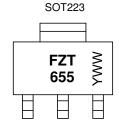
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT655TA	FZT655	7	12	1 000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



FZT 655 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or \overline{W} W = Week Code (01~53)





Absolute Maximum Ratings (@T_A = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	$V_{\sf CEO}$	150	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	lc	1	Α
Peak Pulse Current	I _{CM}	2	Α

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	В	2	W
Power Dissipation	(Note 6)		3	W
Thermal Desistance, Junction to Ambient	(Note 5)	Б	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{0JL}	19.41	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	℃	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

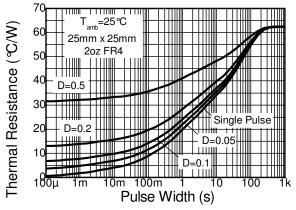
Notes:

- 5. For a device mounted with the collector lead on 25mm X 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 50mm X 50mm single sided 2oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

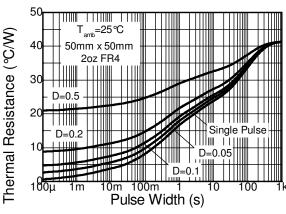
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



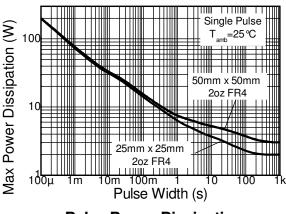
Thermal Characteristics and Derating Information



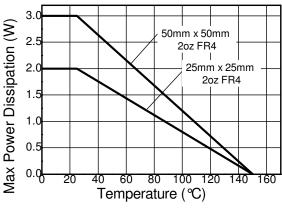
Transient Thermal Impedance



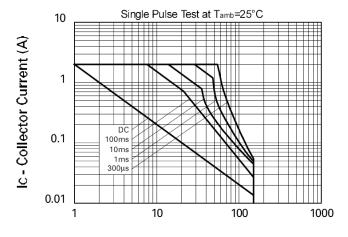
Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve



VCE - Collector Emitter Voltage (V)

Safe Operating Area





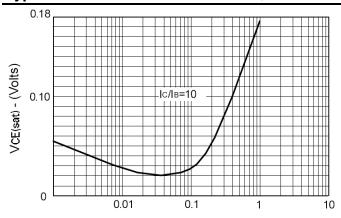
Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	150	-	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	$I_E = 100\mu A$
Collector Cut-off Current	I _{CBO}	_	<10	100	nA	V _{CB} = 125V
Emitter Cut-off Current	I _{EBO}	_	<10	100	nA	$V_{EB} = 5.6V$
Collector Emitter Seturation Voltage (Note O)	V _{CE(sat)}	_	120	500	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		_	180	500		$I_C = 1A$, $I_B = 200mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	0.85	1.1	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Turn-On Voltage (Note 9)	$V_{BE(on)}$	-	0.74	1.0	V	$I_C = 500 \text{mA}, V_{CE} = 5 \text{V}$
	h _{FE}	50	85	_		$I_C = 10$ mA, $V_{CE} = 5$ V
DC Current Gain (Note 9)		50	100	300	_	$I_C = 500 \text{mA}, V_{CE} = 5 \text{V}$
		20	50	_		$I_C = 1A$, $V_{CE} = 5V$
Current Gain-Bandwidth Product	f⊤	30	_	-	MHz	$V_{CE} = 20V$, $I_{C} = 10mA$, $f = 20MHz$
Output Capacitance (Note 9)	C _{obo}	_	_	20	pF	$V_{CB} = 10V$, $f = 1MHz$

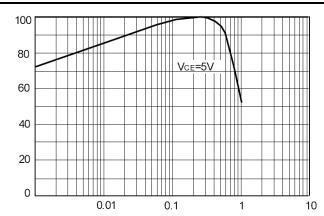
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@ $T_A = +25$ $^{\circ}$ C, unless otherwise specified.)



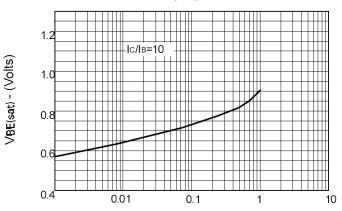
hFE - Normalised Gain (%)



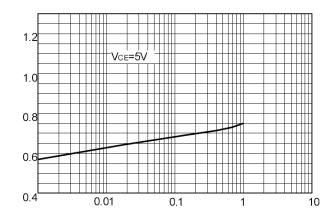
Ic - Collector Current (Amps)

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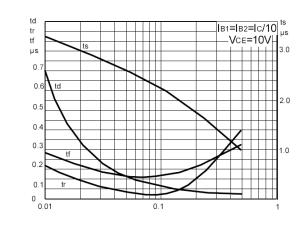
hFE v IC



Ic - Collector Current (Amps)

Ic - Collector Current (Amps)

VBE(sat) v IC



VBE(on) v IC

Ic - Collector Current (Amps)

Switching Speeds

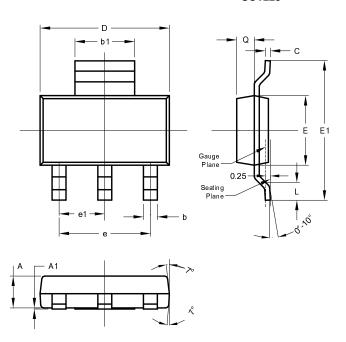
Switching time



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

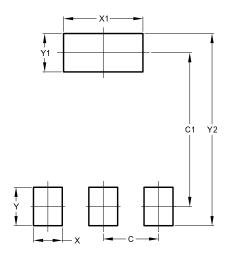
SOT223



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	20.60	30.80	0.70		
b1	2.90	3.10	03.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е		_	4.60		
e1	_	_	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

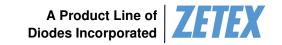
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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